

Silicon NPN Power Transistors

2SC3658

DESCRIPTION

- With TO-3 package
- High voltage ,high speed
- Built-in damper diode

APPLICATIONS

- For color TV horizontal deflection output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

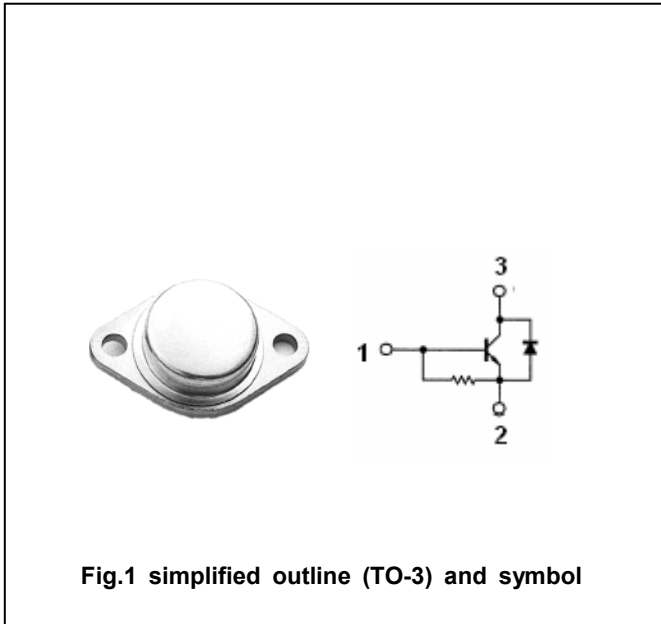


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		5	A
I _{CM}	Collector current-peak		6	A
P _C	Collector power dissipation	T _C =25□	50	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-45~150	□

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A; I _B =1.25A			2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5A; I _B =1.25A			1.5	V
I _{CB0}	Collector cut-off current	V _{CB} =1200V; I _E =0			0.5	mA
I _{EB0}	Emitter cut-off current	V _{EB} =6V; I _C =0			500	mA
h _{FE}	DC current gain	I _C =1A ; V _{CE} =5V	8			
V _{ECF}	Diode forward voltage	I _F =6A			2.0	V
t _r	Fall time	I _C =5A ; I _{B1} =1A; I _{B2} =-2.5A; L _B =0			0.5	μs

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PACKAGE OUTLINE

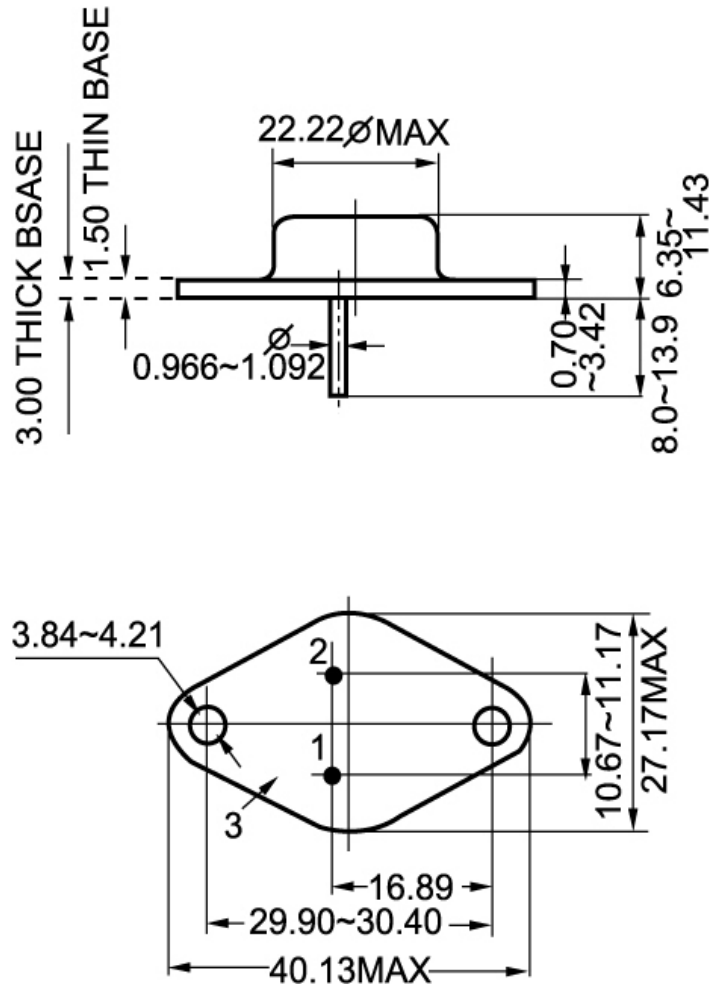


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)